

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (currently amended): An epoxy resin composition for semiconductor encapsulating ~~comprising essentially consisting of~~ an epoxy resin, a phenol resin, an inorganic filler, a curing accelerator, and a carbon precursor having a specific electric resistivity in a semiconductor region of $1 \times 10^4 \Omega\cdot\text{cm}$ or more but less than $1 \times 10^7 \Omega\cdot\text{cm}$, ~~and not containing an organic coloring material~~, wherein the amounts of the inorganic filler and the carbon precursor in the epoxy resin composition are respectively 65-92 wt% and 0.1-5.0 wt%.

Claim 2 (previously presented): The epoxy resin composition for semiconductor encapsulating according to claim 1, wherein the carbon precursor has an H/C ratio by weight determined by elemental analysis of 2/97 to 4/93.

Claim 3 (previously presented): The epoxy resin composition for semiconductor encapsulating according to claim 1, wherein the carbon precursor is fine particles having an average particle diameter of 0.5-50 μm .

Claim 4 (previously presented): The epoxy resin composition for semiconductor encapsulating according to claim 1, wherein the carbon precursor is fine particles having an average particle diameter of 0.5-20 μm .

Claim 5 (canceled).

Claim 6 (previously presented): The epoxy resin composition for semiconductor encapsulating according to claim 1, wherein the amount of the inorganic filler in the total amount of the epoxy resin composition is 70-91 wt%.

Claim 7 (previously presented): The epoxy resin composition for semiconductor encapsulating according to claim 1, wherein the carbon precursor is produced by carbonizing a phenol resin at a calcination temperature of 600-650°C.

Claim 8 (currently amended): A semiconductor device comprising a semiconductor element encapsulated using the epoxy resin composition for semiconductor encapsulating according to any one of claims ~~4-7~~ 1-4, 6 and 7.